FLASH MEMORY-BASED STORAGE SYSTEMS
Today’s Topics

- NAND flash memory
- Flash Translation Layer (FTL)
- OS implications
Flash Memory Characteristics

- Flash memory
  - Non-volatile, updateable, high-density
  - Low cost, low power consumption, high reliability

- Erase-before-write
  - Read
  - Write or Program: 1 → 0
  - Erase: 0 → 1

- Read faster than write/erase

- Bulk erase
  - Erase unit: block
  - Program unit: byte or word (NOR), page (NAND)
NOR Flash

- NOR flash
  - Random, direct access interface
  - Fast random reads
  - Slow erase and write
  - Mainly for code storage
  - Intel, Spansion, STMicro, ...
NAND Flash

- NAND flash
  - I/O mapped access
  - Smaller cell size
  - Lower cost
  - Smaller size erase blocks
  - Better performance for erase and write
  - Mainly for data storage
  - Samsung, Toshiba, Hynix, ...
NAND Flash Architecture

- 2Gb NAND flash device organization

Source: Micron Technology, Inc.
NAND Flash Types

- SLC NAND Flash
  - Small block (≤ 1Gb)
  - Large block (≥ 1Gb)

- MLC NAND Flash

- TLC NAND Flash

Source: Micron Technology, Inc.
## NAND Flash Types

<table>
<thead>
<tr>
<th></th>
<th>SLC NAND&lt;sup&gt;1&lt;/sup&gt; (small block)</th>
<th>SLC NAND&lt;sup&gt;2&lt;/sup&gt; (large block)</th>
<th>MLC NAND&lt;sup&gt;3&lt;/sup&gt;</th>
</tr>
</thead>
<tbody>
<tr>
<td><strong>Page size (Bytes)</strong></td>
<td>512+16</td>
<td>2,048+64</td>
<td>4,096+128</td>
</tr>
<tr>
<td><strong>Pages / Block</strong></td>
<td>32</td>
<td>64</td>
<td>128</td>
</tr>
<tr>
<td><strong>Block size</strong></td>
<td>16KB</td>
<td>128KB</td>
<td>512KB</td>
</tr>
<tr>
<td><strong>t&lt;sub&gt;R&lt;/sub&gt; (read)</strong></td>
<td>15 µs (max)</td>
<td>20 µs (max)</td>
<td>50 µs (max)</td>
</tr>
<tr>
<td><strong>t&lt;sub&gt;PROG&lt;/sub&gt; (program)</strong></td>
<td>200 µs (typ) 500 µs (max)</td>
<td>200 µs (typ) 700 µs (max)</td>
<td>600 µs (typ) 1,200 µs (max)</td>
</tr>
<tr>
<td><strong>t&lt;sub&gt;BERS&lt;/sub&gt; (erase)</strong></td>
<td>2 ms (typ) 3 ms (max)</td>
<td>1.5 ms (typ) 2 ms (max)</td>
<td>3 ms (typ)</td>
</tr>
<tr>
<td><strong>NOP</strong></td>
<td>1 (main), 2 (spare)</td>
<td>4</td>
<td>1</td>
</tr>
<tr>
<td><strong>Endurance Cycles</strong></td>
<td>100K</td>
<td>100K</td>
<td>10K</td>
</tr>
<tr>
<td><strong>ECC (per 512Bytes)</strong></td>
<td>1 bit ECC 2 bits EDC</td>
<td>1 bit ECC 2 bits EDC</td>
<td>4 bits ECC 5 bits EDC</td>
</tr>
</tbody>
</table>

<sup>1</sup> Samsung K9F1208X0C (512Mb)  
<sup>2</sup> Samsung K9K8G08U0A (8Gb)  
<sup>3</sup> Micron Technology Inc.
NAND Applications

- Universal Flash Drives (UFDs)
- Flash cards
  - CompactFlash, MMC, SD, Memory stick, ...
- Embedded devices
  - Cell phones, MP3 players, PMPs, PDAs,
    Digital TVs, Set-top boxes, Car navigators, ...
- Hybrid HDDs
- Intel Turbo Memory
- SSDs (Solid-State Disks)
SSDs

- HDDs vs. SSDs

  2.5” HDD            Flash SSD
  (101x70x9.3mm)

  1.8” HDD            Flash SSD
  (78.5x54x4.15mm)
# SSDs

<table>
<thead>
<tr>
<th>Feature</th>
<th>SSD (Samsung)</th>
<th>HDD (Seagate)</th>
</tr>
</thead>
<tbody>
<tr>
<td>Model</td>
<td>MMDOE56G5MXP (PM800)</td>
<td>ST9500420AS (Momentus 7200.4)</td>
</tr>
<tr>
<td>Capacity</td>
<td>256GB (16Gb MLC x 128, 8 channels)</td>
<td>500GB (2 Discs, 4 Heads, 7200RPM)</td>
</tr>
<tr>
<td>Form factor</td>
<td>2.5” Weight: 84g</td>
<td>2.5” Weight: 110g</td>
</tr>
<tr>
<td>Host interface</td>
<td>Serial ATA-2 (3.0 Gbps)</td>
<td>Serial ATA-2 (3.0 Gbps)</td>
</tr>
<tr>
<td></td>
<td>Host transfer rate: 300MB</td>
<td>Host transfer rate: 300MB</td>
</tr>
<tr>
<td>Power consumption</td>
<td>Active: 0.26W</td>
<td>Active: 2.1W (Read), 2.2W (Write)</td>
</tr>
<tr>
<td></td>
<td>Idle/Standby/Sleep: 0.15W</td>
<td>Idle: 0.69W, Standby/Sleep: 0.2W</td>
</tr>
<tr>
<td>Performance</td>
<td>Sequential read: Up to 220 MB/s</td>
<td>Power-on to ready: 4.5 sec</td>
</tr>
<tr>
<td></td>
<td>Sequential write: Up to 185 MB/s</td>
<td>Average latency: 4.17 msec</td>
</tr>
<tr>
<td>Measured performance¹</td>
<td>Sequential read: 176.73 MB/s</td>
<td>Sequential read: 86.07 MB/s</td>
</tr>
<tr>
<td>(On MacBook Pro, 256KB for sequential, 4KB for random)</td>
<td>Sequential write: 159.98 MB/s</td>
<td>Sequential write: 84.64 MB/s</td>
</tr>
<tr>
<td></td>
<td>Random read: 10.56 MB/s</td>
<td>Random read: 0.61 MB/s</td>
</tr>
<tr>
<td></td>
<td>Random write: 2.93 MB/s</td>
<td>Random write: 1.28 MB/s</td>
</tr>
<tr>
<td>Price²</td>
<td>583,770 won</td>
<td>88,800 won</td>
</tr>
</tbody>
</table>

² Source: [http://www.danawa.com](http://www.danawa.com) (As of Nov. 21, 2010)
NAND Constraints

- No in-place update
  - Require sector remapping (or address translation)
- Bit errors
  - Require the use of error correction codes (ECC)
- Bad blocks
  - Factory-marked & run-time bad blocks
  - Require bad block remapping
- Limited program/erase cycles
  - < 100K for SLCs
  - < 10K for MLCs
  - Require wear-leveling
NAND Constraints

- Limited NOP (Number of Programming)
  - 1 / sector for most SLCs (4 for 2KB page)
  - 1 / page for most MLCs
- Sequential page programming
  - For large block SLCs and MLCs
- Pair-page programming in MLCs
  - Two pages inside a block are linked together
  - Performance difference
  - Interference
A software layer to make NAND flash fully emulate traditional block devices (e.g., disks).

Source: Zeen Info. Tech.
Flash Translation Layer

- Flash cards internals
Flash Translation Layer

- SSDs internals

Source: Mtron Technology
Flash Translation Layer

Flash Cards, SSDs
- Applications
  - Operating System
    - File Systems
    - Block Device Driver
  - Flash Translation Layer
    - NAND Controller
    - NAND Flash Memory

Embedded Flash Storage
- Applications
  - Operating System
    - File Systems
    - Block Device Driver
    - Flash Translation Layer
  - NAND Controller
    - NAND Flash Memory
Flash Translation Layer

- For performance
  - Address translation
  - Garbage collection
  - Hot/cold data identification/separation
  - Interleaving over multiple channels & flash chips
  - Request scheduling
  - Buffer management
  - ...

Flash Translation Layer

- For reliability
  - Bad block management
  - Wear-leveling
  - Power-off recovery
  - Error correction code (ECC)
  - ...

- Other features
  - Encryption
  - Compression
  - Deduplication
  - ...

Page Mapping

- Most flexible
- Efficient handling of small writes
- Large memory footprint
  - One mapping entry per page: 32MB for 32GB MLC (4KB page)
  - Bitmap for page validity
  - Per-block invalid page counter
- Sensitive to the amount of reserved blocks
- Performance affected as the system ages

Data blocks

```
LPN 0
LPN 1
LPN 2
LPN 3
LPN 4
LPN 5
LPN 6
LPN 7
LPN 8
LPN 9
LPN 10
LPN 11
LPN 12
LPN 13
LPN 14
LPN 15
```

Log blocks

```
1'
2'
8'
1''
2''
12'
13'
9'
```

W = <1, 2, 8, 1, 2, 12, 13, 9>
Hybrid Mapping

- Each table entry maps one block
- Small RAM usage
- Inefficient handling of small writes

\[ W = <4, 5, 6, 7, 1> \]
Hybrid Mapping

- Log block scheme [IEEE TOCE 2002]
  - A small number of log blocks
  - 1+ log block(s) per data block
  - Page mapping for log blocks

- Full/partial/switch merge
- Switch merge for sequential updates

- Low log block utilization

W = <1, 2, 8, 1, 2, 12, 13, 9>
Hybrid Mapping

- **FAST [ACM TECS 2007]**
  - Log blocks shared by all data blocks
  - Sequential/random log blocks
  - Improved log block utilization
  - Increased merge time

```
W = <1, 2, 8, 1, 2, 12, 13, 9>
```
Garbage Collection

(a) Switch Merge

(b) Partial Merge

(c) Full Merge
DFTL

OS Implications

- NAND flash has different characteristics compared to disks
  - No seek time
  - Asymmetric read/write access times
  - No in-place-update
  - Good sequential read/sequential write/random read performance, but bad random write performance
  - Wear-leveling
  - ...

- Traditional operating systems have been optimized for disks - What should be changed?
OS Implications

- SSD support in Microsoft Windows 7
  - Turn off “defragmentation” for SSDs
  - New “TRIM” command
    - Remove-on-delete
  - Align file system partition with SSD layout
  - Larger block size proposal (4KB)
Beauty and Beast

- NAND Flash memory is a beauty
  - Small, light-weight, robust, low-cost, low-power, and non-volatile device

- NAND Flash memory is a beast
  - Much slower program/erase operations
  - No in-place-update
  - Erase unit > write unit
  - Limited lifetime (10K~100K program/erase cycles)
  - Bad blocks, ...

- Software support for NAND flash memory is very important for performance & reliability